PRODUCT RELIABILITY REPORT

Product: MP4430_1_2_3
MP9840_1_2_3

Reliability Department
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1. Device Information

<table>
<thead>
<tr>
<th>Product:</th>
<th>MP4430_1_2_3 MP9840_1_2_3</th>
</tr>
</thead>
<tbody>
<tr>
<td>Package:</td>
<td>FCQFN3×4-16</td>
</tr>
<tr>
<td>Process Technology</td>
<td>BCD</td>
</tr>
<tr>
<td>Report Date:</td>
<td>05/02/2017</td>
</tr>
</tbody>
</table>

2. Summary of Test Results

<table>
<thead>
<tr>
<th>Test</th>
<th>Test Condition</th>
<th>Lot# or Date Code</th>
<th>Test Results (S.S./Rej)</th>
<th>Comment</th>
</tr>
</thead>
<tbody>
<tr>
<td>Temperature, Bias, and Operating Life</td>
<td>JESD22-A108, @+125°C for 1000 hours or equivalent</td>
<td>EP366601 EP425100 D1182300</td>
<td>80/0 80/0 80/0</td>
<td></td>
</tr>
<tr>
<td>ESD: Device Charged Model (CDM)</td>
<td>ANSI/ESDA/JEDEC JS-002</td>
<td>D1182300</td>
<td>3/0</td>
<td>&gt;750V</td>
</tr>
<tr>
<td>Latch-up</td>
<td>EIA/JESD78</td>
<td>D1182300</td>
<td>6/0</td>
<td>&gt;+/−100mA &amp; &gt;1.5Vccmax</td>
</tr>
<tr>
<td>Moisture/Reflow Sensitivity</td>
<td>J-STD-020</td>
<td>1536 1549 1612</td>
<td>300/0 300/0 300/0</td>
<td>MSL=1</td>
</tr>
<tr>
<td>High Temperature Storage Life</td>
<td>JESD22-A103, @150°C for 1000 hours</td>
<td>1536 1549 1612</td>
<td>50/0 50/0 50/0</td>
<td></td>
</tr>
<tr>
<td>Accelerated Moisture Resistance- Unbiased Autoclave</td>
<td>JESD22-A102, @121°C/100%RH for 168 hours or equivalent</td>
<td>1536 1549 1612</td>
<td>80/0 80/0 80/0</td>
<td></td>
</tr>
<tr>
<td>Temperature Cycling</td>
<td>JESD22-A104, from 65°C to 150°C for 1000 cycles or equivalent</td>
<td>1536 1549 1612</td>
<td>80/0 80/0 80/0</td>
<td></td>
</tr>
<tr>
<td>Steady State Temperature Humidity Bias Life Test</td>
<td>JESD22-A101, @85°C/85%RH static bias at Vinmax for 1000 hours or equivalent</td>
<td>1536 1549 1612</td>
<td>80/0 80/0 80/0</td>
<td></td>
</tr>
</tbody>
</table>
3. Failure Rate Calculation

Sample Size: 9750
Rejects: 0
Activation Energy (eV): 0.7
Equivalent Device Hours: $7.61 \times 10^8$ Hours
Failure Rate (FIT@60%CL): 1.2 FIT
MTBF (years): 94,880 Year

Revision / Update History

<table>
<thead>
<tr>
<th>Revision</th>
<th>Reason for Change</th>
<th>Date</th>
<th>Rel Engineer</th>
</tr>
</thead>
<tbody>
<tr>
<td>1.0</td>
<td>Initial release</td>
<td>May 2017</td>
<td>Ramon Lei</td>
</tr>
</tbody>
</table>
Appendix: Description of Reliability Test and Failure Rate Calculation

High Temperature Operating Life Test
Purpose: This test is a worst-case life test that checks the integrity of the product. The high temperature testing is use for acceleration of any potential failures over time. The calculation for failure rate (FIT) using the operating ambient temperature is done using the Arrhenius equation.
Condition: 125°C @ Vinmax
Pass Criteria: All units must pass the min/max limits of the datasheet.

ESD Test
Purpose: The purpose of the ESD test is to guarantee that the device can withstand electrostatic voltages during handling.
Condition: Human Body Model and Charged Device Model
Pass Criteria: ESD Testing on every pin. The device must be fully functional after testing and pass the min/max limits in the datasheet.

IC Latch-Up Test
Purpose: The purpose of this specification is to establish a method for determining IC latch-up characteristics and to define latch-up failure criteria. Latch-up characteristics are extremely important in determining product reliability and minimizing No Trouble Found (NTF) and Electrical Overstress (EOS) failures due to latch-up.
Condition: Voltage and current injection
Pass criteria: All pins with the exception of “no connect” pins and timing related pins, shall be latch-up tested. The device must be fully functional after testing and pass the min/max limits in the datasheet.

Moisture/Reflow Sensitivity Classification for Nonhermetic Solid State Surface Mount Devices
Purpose: The purpose of this standard is to identify the classification level of nonhermetic solid state surface mount devices (SMDs) that are sensitive to moisture-induced stress so that they can be properly packaged, stored, and handled to avoid damage during assembly solder reflow attachment and/or repair operations.
Condition: Bake + moisture sock + 3X reflow at 260°C
Pass criteria: All units must pass the min/max limits of the datasheet

Accelerated Moisture Resistance- Unbiased Autoclave
Purpose: To check the performance of the device in humid environments. This test checks the integrity of the passivation, poor metal to plastic seal and contamination level during assembly and material compatibility.
Condition: 121°C/15psig/100% RH (no bias)
Pass Criteria: All units must pass min/max limits of the datasheet

Temperature Cycle Test
Purpose: This test is used to evaluate the die attach integrity and bond integrity. This is similar to the Thermal Shock test, but can generate different failure modes due to the longer dwell time and gradual temperature change.
Condition: -65°C to 150°C
Pass Criteria: All units must pass min/max limits of the datasheet

Power and Temperature Cycling
Purpose: This test method applies to semiconductor devices that are subjected to temperature excursions and required to power on and off during all temperatures. The power and temperature cycling test is performed to determine the ability of a device to withstand alternate exposures at high and low temperature extremes with operating biases periodically applied and removed.
Condition: -40°C to 125°C
Pass Criteria: Function normal on boards. All units must pass min/max limits of the datasheet
Steady State Temperature Humidity Bias Life Test

**Purpose:**
This is to check the performance of the device in humid environments. This test checks the integrity of the passivation, poor metal to plastic seal and contamination level during assembly and material compatibility.

**Condition:**
85%RH at 85°C with Vin=Vinmax

**Pass Criteria:**
All units must pass min/max limits of the datasheet

Highly Accelerated Temperature and Humidity Stress Test

**Purpose:**
This is an equivalent test to Steady State Temperature Humidity Bias Life test with different (higher) temperature stress condition.

**Condition:**
85%RH at 130°C with Vin=Vinmax

**Pass Criteria:**
All units must pass min/max limits of the datasheet

Failure Rate Calculation

The failure rate is gauged by a Failures-In-Time (FIT) based upon accelerated stress data. The unit for FIT is failure per billion device hour.

\[
FIT \text{ Rate} = \frac{\chi^2/2}{EDH} \times 10^9
\]

Where
\[
\chi^2 \text{ (Chi-Squared) is the goodness-of-fit test statistic at a specified level of confidence;}
\]
\[
EDH = \text{Equivalent Device Hours} = AF \times \text{(Life test sample size)} \times \text{(test duration)};
\]
\[
AF = \text{Acceleration Factor}.
\]

High Temperature Operating Life (HTOL) test is usually done under acceleration of temperature and voltage. The total number of failures from the stress test determines the chi-squared factor.

\[
AF = AF_T \times AF_V
\]

The Temperature Acceleration Factor \(AF_T\):

\[
AF_T = \exp\left(\frac{E_a}{K} \left(\frac{1}{T_{J\text{use}}} - \frac{1}{T_{J\text{stress}}}\right)\right)
\]

\(T_{J\text{use}} = \text{Junction temp under typical operating conditions;}
\]
\(T_{J\text{stress}} = \text{Junction temp under accelerated test conditions;}
\]
\(E_a = \text{Activation energy}=0.7eV;
\]
\(K = \text{Boltzmann’s constant}=8.62 \times 10^{-5} \text{ eV/K}.
\]

The voltage Acceleration Factor \(AF_V\):

\[
AF_V = e^{\beta \times (V_{\text{stress}} - V_{\text{use}})}
\]

\(V_{\text{use}} = \text{Gate voltage under typical operating conditions;}
\]
\(V_{\text{stress}} = \text{Gate voltage under accelerated test conditions;}
\]
\(\beta = \text{Voltage acceleration factor (in 1/Volts) and specified by technology.}
\]

Note: For calculation in the report, \(AF_V = 1\) for simplicity.

MTBF (Mean Time Between Failure) equals to \(10^9/FIT\) (in hours).